

and/or said substrate, said layers being arranged in relation to each other such that contiguous layers form a staggered structure on at least one edge of said device, the edge of at least two layers in said staggered structure forming a set of angular or sloped steps where each step has a height corresponding to a thickness of each layer, and at least one electrical edge conductor being provided passing over the edge of one layer and down one step at a time enabling connection to an electrical conductor in any of the layers following in the staggered structure.

2. (Amended) The memory and/or data processing device according to claim 1, wherein said at least one electrical conductor is provided passing over the edge of said staggered structure and connecting electrically to in-layer conductors in two or more and up to a plurality of contiguous layers, negotiating one step at a time.

3. (Amended) The memory and/or data processing device according to claim 2, wherein said in-layer conductors form electrical connections between electrical conductors negotiating the step up to the contiguous layer above and/or down to the contiguous layer below.

4. (Amended) A method for manufacturing a memory and/or data processing device having at least two stacked layers overlapping each other partially or completely, said layers being supported by a substrate or alternatively forming a sandwiched self-supporting structure of such stacked layers, and at least two layers in the stack comprise memory and/or processing circuitry connecting electrically to memory and/or processing circuitry in at least one other layer and/or substrate, and the method comprising the steps of

adding said layers successively, one layer at a time such that the layers form a staggered structure, and

providing one or more layers with at least one electrical contacting pad for linking to one or more interlayer edge connectors.

5. (Amended) The method according to claim 4, further comprising providing said layers on a supporting substrate, and forming said staggered structure as a step pyramid.

6. (Amended) The method according to claim 4, further comprising providing said layers on a supporting substrate and forming said staggered structure as an inverted pyramid, each of said layers connecting to said substrate via said electrical edge connectors negotiating a single step.

7. (Amended) The method according to claim 4, further comprising forming said edge connectors in a process selected from one of lithography, dry etching, inkjet printing, silk screen printing, soft lithography, electrolysis, electrostatic deposition and in situ conversion.